Nonequilibrium wetting transitions with short range forces

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W e analyze within m ean-eld theory as well as num erically a K P Z equation that describes nonequilibrium wetting. Both complete and critical wetting transitions were found and characterized in detail. For one-dimensional substrates the critical wetting temperature is depressed by uctuations. In addition, we have investigated a region in the space of parameters (temperature and chemical potential) where the wet and nonwet phases coexist. Finite-size scaling analysis of the interfacial detaching times indicates that the nite coexistence region survives in the therm odynamic limit. W ithin this region we have observed (stable or very long-lived) structures related to spatio-tem poral interm ittency in other system s. In the interfacial representation these structures exhibit perfect triangular (pyramidal) patterns in one (two dimensions), that are characterized by their slope and size distribution.

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I. IN TRODUCTION

W hen a bulk phase is placed into contact with a substrate, a layer of a second, coexisting, phase m ay form if the substrate preferentially adsorbs it. At a wetting transition, the thickness of the layer diverges. Equilibrium wetting has been experimentally observed and theoretically investigated using, am ong m any other techniques, interface displacement models [1, 2, 3]. W ithin this approach one considers the local height of the interface m easured from the substrate, h (x), and constructs an effective interface H am iltonian, H (h) [4]. In equilibrium situations, one typically has

H (h) =
$$\frac{Z_1}{dx} \frac{\#}{2} (r h)^2 + V (h)$$
 : (1)

where is the interfacial tension of the interface (or the interfacial sti ness if the medium is an isotropic) and V (h) accounts for the interaction between the substrate and the interface.

If all the m icroscopic interactions are short-ranged, one m ay take for su ciently large h at bulk coexistence [3]

$$V(h) = b(T)e^{h} + ce^{2h}$$
; (2)

where T is the tem perature, b(T) vanishes linearly as T T_W , T_W being the wetting tem perature, and c > 0[5]. By minimizing (1) one nds [1, 3] a critical wetting transition at b = 0, i.e. the interface height (or equivalently, the wetting layer thickness), hhi, diverges continuously as b T T_W ! $b_W = 0$. Equilibrium critical wetting has been studied for decades and a rich (non-classical) behavior predicted [1, 2].

W etting transitions may also be driven by the chem ical potential di erence between the and phases, . In this case wetting occurs at any temperature above T_W (i.e. for $b > b_W$) as = 0 is approached from the phase.

This is always a continuous transition and it is known as complete wetting [1]. A study of complete wetting requires adding a linear term h to the Ham iltonian (1).

A dynam ic m odel for the grow th of wetting layers has been proposed through the Langevin equation [6]

$$(t_t, t_t) = \frac{H}{h} + = r^2 h \frac{\theta V}{\theta h} + ;$$
(3)

where is Gaussian white noise with mean and variance

h (x;t)
$$i = 0;$$

h (x;t) (x⁰;t⁰) $i = 2D$ (t t⁰) (x x⁰): (4)

Equation (3) is an Edwards-W ilkinson (EW) growth equation [7, 8] in the presence of an elective interface potentialV (h). It describes the relaxation of the interfacial height h towards its equilibrium value, i.e. the value of h that m inimizes H.W ithin this context can be viewed as an external driving force acting on the interface. Recall that in the absence of the wall, the corresponding equilibrium states for < 0 and > 0 are the and phases, respectively, whereas phase coexistence occurs at = 0.

Equilibrium models, however, are not su cient to study wetting in Nature, since in a wide range of phenomena (e.g., growth of thin Ims, spreading of liquids on solids or crystal growth) therm all equilibrium may not hold. Nonequilibrium wetting transitions have been recently studied by Hinrichsen et al. [9] in a lattice (restricted solid-on-solid) model with dynamics that do not obey detailed balance. The continuum nonequilibrium counterpart of this discrete model, is a Kardar-Parisi-Zhang (KPZ) equation in the presence of a bounding potential, whose properties have been analyzed extensively by one of the authors and collaborators [11, 13]. C learly this is the most natural extension of the EW equilibrium growth model to non-equilibrium situations. In fact, in the absence of a substrate the KPZ non-linearity, $(r h)^2$, is generically the most relevant nonequilibrium perturbation to the equilibrium EW equation [8]. The KPZ nonlinearity is related to lateral growth, and although this mechanism is unlikely to be relevant in simple uids, it may determ ine the wetting behavior of systems with anisotropic interactions for which the growth oftilted interfaces depends on their orientation [14]. For instance, it has been shown that crystal growth from atom ic beam s is described by the KPZ equation [15]. From a theoretical point of view a key and ambitious task is that of developing general criteria to establish whether the KPZ non-linear term should be included in a given interfacial m odel.

R elated works published recently by M uller et al. [16], G iada and M arsili [17], H inrichsen et al. [18], and ourselves [10], consider sim ilarnon-equilibrium m odels in the presence of various types of walls.

In this paper, we further study the KPZ interfacial equation in the presence of di erent types of potentials, attractive and repulsive. We focus on the connection of the associated phenom enology with non-equilibrium wetting and depinning transitions. In particular, we will stress that the transitions called \ rst-order non-equilibrium wetting "in [18] are not wetting transitions but, rather, depinning transitions. A lso, we study for the rst time the two-dimensional version of this model, and

report on new phenom enology.

The remainder of this paper is organized as follows. In the next section we introduce our KPZ-like model. A mean-eld picture is provided in section III, and its predictions numerically tested in section IV. The conclusions are summarized in the nal section.

II. THE MODEL

The model under study is de ned by the Langevin equation

$$(t_t, t_t) = r^2 h + (r h)^2 - \frac{(0 V (h))}{(0 h)} + ;$$
(5)

where V (h) = $(a+1)h+be^{h}+ce^{2h}=2, c>0$, obeys (4) and a+1= is a chemical potential.

In the absence of the exponential terms (the limiting wall) the interface moves with a nonzero positive (negative) mean velocity for larger (smaller) than a certain critical value $_{\rm c}$. In one dimension $_{\rm c}$ can be found analytically since both the KPZ and EW equations have the same G aussian steady-state height distribution [8]. Thus $_{\rm c} = h(r h)^2 i$, which for discrete lattices can be approximated by [19] $_{\rm c} = (D) = (2)$, being the lattice cuto. Note that for $\frac{6}{10}$ 0 a nonzero chemical potential is required to balance the force exerted by the nonlinear term on the tilted interfacial regions. For = 0 the model reduces to the equilibrium one and $_{\rm c} = 0$ as usual. For negative values of the interface is (on average) pushed against the wall, while for positive it is

pulled away from the wall. Thus the behavior of the system is determined by the sign of [20]. In this paper we will consider < 0 only (which corresponds to the case studied using m icroscopic models [18]). Results for positive values of will be published elsewhere.

It is our purpose to study the e ects of a substrate that adsorbs preferentially one of the two phases on the stationary properties of the interface. This is achieved by considering b to be negative in equation (5).

This same equation, (5), has been recently studied by G iada et al. [17] as a generic nonequilibrium continuum m odel for interfacial growth. However, their choice of controlparam eters [17] privileges the role of the noise as the driving force of the nonequilibrium transitions. By contrast, m otivated by the role of the chemical potential and temperature in equilibrium wetting, we x the noise intensity and choose a and b as controlparam eters that are the elds driving critical and com plete wetting transitions.

To establish the analogy with equilibrium , let us stress that just like in equilibrium complete wetting, nonequilibrium complete wetting occurs when the attractive potential V (h) is not capable of binding the interface, at temperatures above the wetting transition temperature, $b > b_W$, as the chem ical potential approaches that of bulk coexistence', ! ... At this transition the interface begins to move and hhi diverges. On the other hand, the nonequilibrium analogue of critical wetting corresponds to the unbinding of a bound interface at bulk coexistence', = ..., as b! b_W .

In order to analyze equation (5) it is convenient to perform a Cole-H opt change of variable $h(x;t) = \ln n(x;t)$, leading to

$$@_tn = r^2n \quad \frac{@V(n)}{@n} + n;$$
(6)

with V (n) = $an^2=2 + bn^3=3 + cn^4=4$. This describes the interface problem as a di usion-like equation with multiplicative noise [11, 21]. In this representation, the unbinding from the wall (hhi! 1) corresponds to a transition into an absorbing state hni! 0. In the following we will use both languages, h and n, indistinctly although the natural description of wetting is in terms of h. The case b> 0 was studied in [9, 11], while b< 0 is the case studied in [10, 16, 17, 18, 22].

Note that we have made use of Ito calculus, and thus equation (6) should be interpreted in the Ito sense [23]. In general, potentials of the form $\ln^{p+2} = (p+2) + \ln^{2p+2} = (2p+2)$ with p > 0 result in equivalent e ective Ham iltonians since, when expressed in terms of h, p can be eliminated by rede ning the height scale. The case p = 2 (with xed b < 0) has been studied in [22] in the context of stochastic spatio-tem poral interm ittency (ST I). The unsuspected connections between these two problem s are illustrated in the following sections. In this section we analyze equation (6) at the mean eld level. We begin by discretizing (6) on a regular ddimensional lattice

$$\varrho_{t}n_{i} = \frac{X}{2d} (n_{j} - n_{i}) \frac{\varrho_{V}(n_{i})}{\varrho_{n_{i}}} + n_{i} ;$$
(7)

where $n_i = n \langle x_i; t \rangle$ and the sum over j runs over the nearest neighbors of i. The Fokker-P lanck equation for the one-site stationary probability P (n_i) can be easily worked-out. In m ean-eld approximation (i.e. substituting the values of the nearest neighbors by the average n value), the stationary Fokker-P lanck equation for D = 1 is

$$\frac{\theta}{\theta n} \frac{\theta V(n)}{\theta n} + (n - hni)P_t(n) + \frac{\theta^2}{\theta n^2} n^2 P_t(n) = 0 \quad (8)$$

and its associated solution

ъ

$$P(n;mi) = N \frac{1}{n^2} \exp \left(\frac{\sum_{n=1}^{n} V^{0}(n) + (n - mi)}{n^2} dn; \right)$$
(9)

where the integration constant N is determined by a normalization condition and hni is obtained from the selfconsistency requirement

$$mi = \frac{\frac{1}{10} \operatorname{dn} nP(n; mi)}{\frac{1}{10} \operatorname{dn} P(n; mi)} = F(mi):$$
(10)

Let us consider two limiting cases where analytic solutions of Eq.(10) can be worked out. In the zerodimensional case, or equivalently = 0, the solution of (8) reads

$$P(n) = N \frac{\exp \left(\frac{b}{p}n^{p} + \frac{c}{2p}n^{2p}\right)}{n^{a+2}};$$
 (11)

that, in terms of heights, is P (h) exp[(a + 1)h be h =p ce 2h =2p] and yields the elective potential $V_{eff}(h) = lnP(h) = (a + 1)h + be^{h} =p + ce^{2h} =2p$. Clearly this coincides with the potential in (5). A com - plete wetting transition occurs when approaching a = 1 with b > 0 and critical wetting is found at a = 1 with b = 0.

For spatially extended systems, in the = 1 limit, a saddle-point expansion in yields V⁰(n) = 0 [17, 24]. Thus, the dynam ical behavior in this limit is that of the determ inistic m ean-eld version of (8): for any p > 0, there is a line of second order wetting transitions at a = 0and b > 0, and a line of rst-order transitions at a > 0and b = (p + 2) ac=(p + 1). These lines meet at a tricritical point at the origin.

For values of other than zero or 1, the selfconsistency equation hni = F(mi) has to be solved numerically. W ithout loss of generality, we set p = 2, c = 1, and illustrate in Fig. 1 the three di erent regimes: one

stable solution at hni = 0 (dash-dotted line); one unstable solution at hni = 0 and a stable one at $hni \neq 0$ (solid line); two stable solutions and an unstable one (dashed line). Stable solutions can be identied by a negative slope of F (hni) hni at the intersection point [25]. A nonzero solution em erging continuously from hni = 0 as a function of a and b, signals a second order transition. This is the case for the dash-dotted and the solid lines in the inset of Fig. 1. By contrast, when the nontrivial solution appears discontinuously as a function of a and b, the transition is rst-order (dash-dotted and dashed lines). The corresponding phase diagram is depicted in Fig. 1. The solid line is a second-order phase boundary from non-wet to wet substrates. Between the two dotted lines, the wet and non-wet phases coexist as stationary solutions of the dynam ical equation. The three lines join at the tricritical point at a = b = 0.

In order to determ ine the order parameter critical exponent in mean eld approximation, we proceed as in [13]. First, we rewrite (10) as

$$\operatorname{mi}^{1} = \operatorname{e}_{\operatorname{mi}} \operatorname{ln} \operatorname{dtt}^{a} \exp \frac{b}{p} \operatorname{t}^{p} \frac{t^{2p}}{2p} e^{\operatorname{mit}}:$$
(12)

Next, we introduce a Gaussian transformation and expand the resulting integrals for small hni. We nd hni $j_a j^{1=p}$, and thus $a_c = 0$ and = 1=p.

IV. BEYOND MEAN FIELD THEORY

In this section we explore whether the mean-eld phase diagram structure survives when the e ects of uctuations are taken into account. Mean-eld exponents are expected to hold above the upper critical dimension d_c , which in the present case, equation (6), is known to be $d_c = 2$, (corresponding to 3 bulk dimensions and in the weak coupling regime of the KPZ) [11]. For positive values of b and d > 2, the second term n^{2p+2} in the e ective potential is irrelevant [11] and the we are left with

$$Q_t n = r^2 n \quad an \quad bn^{p+1} + n;$$
(13)

de ning the multiplicative-noise (M $\rm N$) universality class [11].

W e have solved (6) num erically for di erent system dim ensions. In particular, for a one-dim ensional substrate we have considered a system size L = 1000, = p = 2, D = 1 and c = 1.5. The time step and the mesh size were set to 0.001 and 1, respectively. W e started by determ ining the chem ical potential for which the free interface has zero average velocity. For the param eters given above we found a_c 0.064. Then we x a = a_c and calculate hn (t)i for di erent values of b and large t. Length and tim e units are in lattice spacings and M onte C arlo steps, respectively.

A. Criticalwetting

To study critical wetting we set $a = a_c$ and consider sm all values of b for w hich an initially pinned interface remainspinned, and increase progressively buntil the nonwet phase becomes unstable at b_W . The critical point is estim ated as the value by that maxim izes the linear correlation coe cient of loghn i versus log to bw ; the critical exponent is then determ ined from the corresponding slope (Fig. 2). It is found that the critical \tem perature" is depressed from its mean-eld value $b_W = 0$ to $b_{W} = 0.70 \quad 0.01$, with an associated critical exponent = 1:20 0:01 (the error in the exponent com es from a least-squares t). Below (above) that value we nd rst (second) order depinning transitions, by varying a. Therefore, as in mean eld, there is a \tricritical " point, joining a line of second order transitions (b > b_w) with one of rst order transitions (b < $b_{\!W}$). The critical exponents and universality of this multiplicative-noise tricritical point has not been investigated before.

The nite coexistence region allow sus to de ne critical wetting along a range of di erent paths, delim ited by the dashed lines in the mean-eld diagram of Fig. 1. We have checked that the value of does not change when the critical point is approached along di erent paths within this region. Further num erical and analytical studies of this new universality class will be left for future work.

B. Complete W etting, $b > b_W$ case

W e consider a one-dim ensional substrate, with b = 1 > $b_{\!\scriptscriptstyle W}$, let the system evolve to the stationary state and then com pute the order param eter hni for di erent values of a near its critical value. As a ! ac a continuous transition into an absorbing state n = 0 is observed; it is the nonequilibrium counterpart of com plete-wetting. The associated critical exponent is found to be = 1:65 0:05 in good agreem ent with the prediction for the M N class, = 1:5 0:1 [13]. O therpositive values of by jeld similar results. In addition, we have simulated systems above the upper critical dimension, in d = 3, with L = 25, b = 5 and other parameters as in the one-dimensional case. Our best estimate for is = 0:96 0:05, indicating that this transition is governed by the weak noise xed point of the MN class [11]. For larger values of the noise amplitude we nd a strong coupling transition, in agreem ent with the theoretical predictions [11, 13]. Finally, we note that both num erical and renorm alization group arguments lead to = 1 in the weak coupling regime, independently of the value of p [11]. This is at odds with the mean-eld prediction = 1=p. Birner et al. [?] have recently suggested a transition from 1=p to a nonuniversalbehavior depending on the ratio of the noise to the strength of the spatial coupling. However, this discrepancy appears to be generic since di erent types of mean-eld approaches yield the same (incorrect) result and the origin of the discrepancy rem ains unclear [13].

Since the Cole-H opf transform of the M N equation is the same as K P Z with an additional exponential term, the M N exponents are those of K P Z i the extra term is an irrelevant term of the K P Z renorm alization group ow. Note that the Cole-H opf transform xes the value of = and thus the = 0 limit can not be considered when this transform ation is used. In addition the potential V (h) is a relevant term of the EW equation. In this regim e adding a non-linear potential is a relevant perturbation and it does indeed change/determ ine the wetting exponents (cf. with the literature on equilibium wetting [1]). Thus EW plus a (non-linear) wetting potential is not equivalent to K P Z in the weak coupling regim e plus the sam e wetting potential.

C . Depinning transition at $b < b_{\!\scriptscriptstyle W}$

As expected, no transition is found as a $! a_c$ when equation (6) is solved numerically for b < $b_{\!\scriptscriptstyle M}$. Of course, the system undergoes a pinning/depinning transition when crossing the $a_c = 0$ boundary line, but this transition is driven by the chem ical potential di erence rather than by the substrate potential and thus it is unrelated to wetting, where phase coexistence of the \liquid" and $\gas"$ phases is required (i.e. $a = a_c$). A very rich phenom enology associated with these transitions. have been found, however. For b = 4 we nd that the nonwet phase becomes unstable at a 1:3 and that the wet phase becom es unstable at a_c 0:064 (as before). Consequently, in the range $a_c < a < a$ both phases coexist. This means that if the interface is initially close to the wall (n > 1) it remains pinned, while if it is initially far from the wall (n < 1) it detaches and moves away with a constant velocity. Therefore, the system undergoes a rst-order transition as a function of a. In order to establish the phase boundaries we have used the following criteria. The stability of the pinned phase may be characterized by the time taken by the interface to depin in the limit L! 1. can be de ned as the time taken by the last site of the interface to detach, h(x) > 0 or n(x) < 1 8x. Similarly, we may de ne

as the time characterizing the asymptotic exponential decay of hn (t) i, where the angular brackets denote averages of independent runs (typically 10⁵ 10⁶ in our simulations). We have veried that both de nitions yield analogous results. As shown in Fig. 3A, for a > a, saturates with increasing system size and thus the interface detaches in a nite time. Within the coexistence region we have found two di erent regimes: close to the stability threshold of the pinned phase there is a narrow stripe 1:22 < a < 1:3 where the detaching time grows approximately as a power-law. For a $^{<}$ a $^{<}$ 1.22 grows exponentially with L. In both cases diverges as L ! 1, implying that the pinned phase is stable in the therm odynam ic lim it. Due to the very large characteristic times, we cannot discard the possibility that the power-laws are also (asymptotically) exponentials. The

study of the asym ptotic behavior of the detaching times requires longer simulations, beyond our current computer capabilities. Finally, the non-monotonic behavior of the characteristic times, as well as the step in the curve for a = 1.28, may be accounted for by the presence of two different competing mechanisms as described in [10]: once a site is detached it pulls out its neighbors which, in turn, pullout their neighbors in a cascade e ect until the whole interface is depinned in a time which grows a linearly with L. This is more likely for small system s, but the probability that a site gets detached increases with the system size.

A nother way to characterize the power-law regime is to analyze the single-site stationary probability density function (ss-pdf), de ned as the average of n(t) over pinned states rather than over all runs. Figure 3 shows the unnormalized ss-pdf for di erent values of a. In the exponential-regime (a < 1.22) the histogram exhibits a maximum at a pinned state with hni > 0. In the powerlaw-regime, how ever, the histogram develops a secondary maximum nearn = 0, indicating that a fraction of the interface depins. As a increases, the secondary maximum, at zero n, increases while the maximum, at nite n, decreases. At the stability edge (a 1:3) the histogram changes abruptly into a delta function at n = 0 and the pinned phase becom es unstable.

The di erences between the exponential and power-law regin es are also observed in a space-time snapshot of a num erical solution of (6). In Fig. 4 we plot the stationary eld n, for a = 1.28, exhibiting patterns characteristic of ST I [2]. The main feature of these patterns is the appearance of depinned patches (absent for values of a in the exponential regin e) with a wide range of sizes and life-times within the pinned phase. This regin e, overboked in previous studies of nonequilibrium depinning transitions [17, 18], seem s to correspond to the power-law regin e described earlier. It is therefore restricted to a narrow range between the exponential and the depinned regim es. This nding is at odds with results of previous work claim ing that ST I is generic in the coexistence region [22].

A typicalpro le in term s of h is shown in Fig. 5. The depinned interfacial regions form triangles with constant average slope s. These triangular droplets are sim ilar to those described in the discrete m odel of [18]. By taking averages of (5), the typical slope, s, of the triangular facets is determined through

$$j_R j_s^2 = a + 1;$$
 (14)

where $_{\rm R}$ is the renorm alized non-linear coe cient of the KPZ equation. In order to verify equation (14) we have xed = p = D = 1, = 1 and a = 2:16. A veraging over 250.000 di erent triangles, we nd an average slope s = 1:781, while the value of $_{\rm R}$ calculated from the tilt-dependent velocity of the depinned interface [8] yields $_{\rm R}$ = 0:9934 from which s = 1:784, in excellent agreem ent with the previously measured value.

W e also studied the size distribution of triangles within

the power-law regime. Our results correspond to = p =D = 1, = 1, L = 500, b = 4, and the following valuesofa: 2:12;2:14;2:15, and 2:16, and are sum m arized in Fig. 6. a 2:10 is the boundary between the power-law and exponential regimes and the pinned phase is unstable for a 2:18. The maximum size of the depinned regions increases as this instability is approached. Our data suggests an exponential dependence on the size of the triangular base. This indicates that there is a maxin um size for the depinned regions and thus rigorous scale invariance (typical of growth driven by a coarsening m echanism) of the ST I region is ruled out. M ore explicitly, the distribution of triangle sizes, l, is described very well by the function exp [3:44 (a 2:176) 1], in plying that the exponential slopes in Fig. 6 are proportional to a . Clearly, triangles with a base less than 2:3 cannot be visualized due to the discretization of equation (6). A simple extrapolation indicates that the triangles become imperceptibly small for a 2:05, in good agreem ent with the value obtained for the boundary between the power-law and exponential regimes. Therefore, we cannot rule out the possibility that the triangles are ubiquitous throughout the coexistence region (although not always visible in a discrete num erical simulation) in which case the power-law dettaching times should turn into exponentials for large enough times and system sizes. In this case the force exerted by the non-linear KPZ term on the triangular facets against the direction of growth, at late times, quarantees the stability of the pinned phase [18] throughout the nite coexistence region.

Finally, we study the phase-coexistence regime in a two-dimensional system to check whether the triangular patterns survive in higher dimensionalities. In particular, we consider a system size 100 100 and take a = 2, b = 4, well within the coexistence region. We nd structures as those shown in Fig. 7: the triangles becom - ing pyram ids. Note that the edges of the pyram id bases are parallel to the axes of the discretization-lattice. This suggests that the pyram ids are lattice artefacts and that a continuum system m ay exhibit conical structures.

V. CONCLUSIONS

We have investigated a continuum model for nonequilibrium wetting transitions. The model consists of a K P Z equation in the presence of a short-ranged substrate potential, and is the most natural non-equilibrium extension of the interface displacement models used in equilibrium wetting. It can be mapped into a multiplicative noise problem, enabling simple theoretical calculations at the mean- eld level. Numerical simulations reproduce a phase diagram analogous to that obtained within meaneld, including rst as well as second-order phase transitions. In particular, we have found complete wetting and critical wetting transitions, as well as a nite area in the tem perature-chem ical potential phase diagram where pinned and depinned phases coexist. This nite coexistence region allows us to de ne critical wetting along a range of paths that are, how ever, characterized by the same critical exponents. W ithin this area we identied two regimes. In the rst, the lifetime of the pinned phase grows exponentially with increasing system size and its sspdf is bell-shaped. The second one exhibits ST I, lifetimes consistent with a power-law, and a double-peaked sspdf. The main feature of the latter regime is the presence of triangular structures that have been characterized by their slopes and size distributions.

An interesting open problem is that of the equilibrium lim it of non-equilibrium wetting. The Cole-H opf transform precludes the lim it = 0 to be studied using this method. Moreover, we have noted how the behavior of the EW equation in the presence of a wetting potential di ers from the weak-noise regime of the MN equation. This leaves the crossover to equilibrium wetting an open challenge. In addition, the e ects of long-ranged potentials on the phenom enology described here remain to be investigated.

Finally it would be extremely interesting to develop experiments in order to explore the rich, non-equilibrium phenomenology described in the previous sections; liquidcrystals are in our opinion good candidates for this. It is our hope that this work will stimulate experimental studies in this direction.

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- [5] If, instead, one considers long-range (van der W aals) interactions, the potential has the general form [1].

$$V(h) = b(T)h^{m} + ch^{n}; n > m > 0:$$
 (15)

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FIG.1: Mean-eld phase diagram and typical solutions of the equation F (mi) = hni (tem perature in units such that $k_{\rm B}$ = 1.



FIG.2: Top: linear correlation coe cient for $\ln n$ as function of \ln b $_W$ j for di erent values of b_W . The maximum gives the best estimate of b_W = 0:70 0:01. Bottom : log-log plot of $\ln n$ as function of \ln b $_W$ j in the vicinity of the critical point. The line is a least-squares t; from its slope the critical wetting exponent is found to be 1:20 0:02



FIG.3: (A) Characteristic depinning times and (B) ss-pdf for various representative values of a.



FIG. 4: C on guration in the n-representation for a = 1:18 and b = 4. D epinned regions (n < 1) are colored in darkgrey and pinned ones (n > 1) in light-gray. 1000 time slices are depicted at intervals of 50 time units. The system size is L = 500.



FIG. 5: Instantaneous con guration of the interface for time slice 400 (m arked with a line in Fig. 4). Param eters as in Fig.



FIG. 6: D is tribution of triangles as a function of the size of the triangular base, for a = 2.12;2.14;2.15 and 2.16.



FIG.7: Snapshot of an interface conguration for a 100 100 system (not all the substrate is shown) and parameters a = 2 and b = 4.